

Miguel Fernandes

List of Publications by Citations

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159
papers

532
citations

11
h-index

17
g-index

181
ext. papers

613
ext. citations

2.8
avg, IF

2.78
L-index

#	Paper	IF	Citations
159	Laser-scanned p-i-n photodiode (LSP) for image detection. <i>IEEE Sensors Journal</i> , 2001 , 1, 158	4	51
158	Self-biasing effect in colour sensitive photodiodes based on double p-i-n a-SiC:H heterojunctions. <i>Vacuum</i> , 2008 , 82, 1512-1516	3.7	26
157	Improved Resolution in A P-I-N Image Sensor by Changing the Structure of the Doped Layers. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 609, 1421		22
156	Image capture devices based on p ⁺ silicon carbides for biometric applications. <i>Journal of Non-Crystalline Solids</i> , 2002 , 299-302, 1245-1249	3.9	21
155	Transport mechanism in high resistive silicon carbide heterostructures. <i>Applied Surface Science</i> , 2001 , 184, 144-149	6.7	20
154	Large area image sensing structures based on a-SiC:H: a dynamic characterization. <i>Sensors and Actuators A: Physical</i> , 2004 , 113, 360-364	3.9	19
153	Pinp ⁺ and pinp ⁺ multilayer devices with voltage controlled optical readout. <i>Journal of Nanoscience and Nanotechnology</i> , 2009 , 9, 4022-7	1.3	15
152	Optical multiplexer for short range communications. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2009 , 41, 1082-1085	3	13
151	ITO/SiO _x /Si optical sensor with internal gain. <i>Sensors and Actuators A: Physical</i> , 2001 , 92, 152-155	3.9	13
150	Optical Readout in Pinp ⁺ and Pinp ⁺ Imagers: A Comparison. <i>Materials Research Society Symposia Proceedings</i> , 2007 , 989, 4		12
149	Image and color sensitive detector based on double p-i-n/p-i-n a-SiC:H photodiode. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 862, 1341		12
148	Bias sensitive multispectral structures for imaging applications. <i>Thin Solid Films</i> , 2007 , 515, 7566-7570	2.2	11
147	Stacked n-i-p-n-i-p Heterojunctions for Image Recognition. <i>Materials Research Society Symposia Proceedings</i> , 2003 , 762, 18131		11
146	Influence of the band offset on the performance of photodevices based on the c-Si/a-Si:H heterostructure. <i>Thin Solid Films</i> , 2001 , 383, 314-317	2.2	10
145	A new CLSP Sensor for Image Recognition and Color Separation. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 715, 431		10
144	Surface-barrier Si-based photodetectors fabricated by the spray pyrolysis technique. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 2000 , 80, 781-790		10
143	Inhomogeneous transport in microcrystalline p-i-n devices. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 2000 , 80, 755-764		9

142	Controlling the Lateral Photoeffect in a-Si:H Heterojunction Structures: The Influence of the Band Offset Analysed Through A Numerical Simulation. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 664, 25111		9
141	Voltage controlled amorphous Si/SiC photodiodes and phototransistors as wavelength selective devices: Theoretical and electrical approaches. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1153, 1		8
140	An amorphous SiC/Si image photodetector with voltage-selectable spectral response. <i>Thin Solid Films</i> , 2006 , 511-512, 167-171	2.2	8
139	Image processing in a μ -Si:H p μ image transducer. <i>Journal of Non-Crystalline Solids</i> , 2000 , 266-269, 1228-1232	3.9	8
138	Near-infrared photodetectors based on a HgInTe-semiconductor compound 1999 ,		8
137	Photocurrent multiplication in ITO/SiO _x /Si optical sensors. <i>Vacuum</i> , 2002 , 65, 67-71	3.7	7
136	Optoelectronic characterization of a-SiC:H stacked devices. <i>Journal of Non-Crystalline Solids</i> , 2004 , 338-340, 345-348	3.9	7
135	Image and color recognition using amorphous silicon p μ photodiodes. <i>Sensors and Actuators A: Physical</i> , 2005 , 123-124, 326-330	3.9	7
134	UV/Visible ITO/GaP Photodiodes: Characterization and Modeling. <i>Physica Status Solidi A</i> , 2001 , 185, 137-144		7
133	New p μ Si:H imager configuration for spatial resolution improvement. <i>Sensors and Actuators A: Physical</i> , 2001 , 92, 60-66	3.9	6
132	Optical demultiplexer device operating in the visible spectrum. <i>Sensors and Actuators A: Physical</i> , 2011 , 172, 35-39	3.9	5
131	Large area double p μ heterostructure for signal multiplexing and demultiplexing in the visible range. <i>Thin Solid Films</i> , 2009 , 517, 6435-6439	2.2	5
130	LSP image sensors based on SiC heterostructures. <i>Applied Surface Science</i> , 2001 , 184, 471-476	6.7	5
129	Readout improvement in large area a-SiC:H-based image sensors. <i>Applied Surface Science</i> , 2001 , 184, 408-412	6.7	5
128	Tailored Laser scanned photodiodes (LSP) for image recognition. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 664, 1851		5
127	Carrier transport and photogeneration in large area p-i-n Si/SiC heterojunctions. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 664, 25101		5
126	Dependence of the Lateral Photoeffect in a-Si:H P-I-N Structures on the Material Characteristics Studied by Means of a Numerical Simulation. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 715, 771		5
125	Three Transducers Embedded into One Single SiC Photodetector: LSP Direct Image Sensor, Optical Amplifier and Demux Device 2011 ,		4

124	Colour sensitive devices based on double p-i-n-i-p stacked photodiodes. <i>Thin Solid Films</i> , 2007 , 515, 7526-7529	4
123	The laser scanned photodiode: Theoretical and electrical models of the image sensor. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 1801-1804	3.9 4
122	Optically addressed read/write device based on tandem heterostructure. <i>Journal of Non-Crystalline Solids</i> , 2004 , 338-340, 754-757	3.9 4
121	A μ c-Si:H P-I-N Imager For 2-D Pattern Recognition. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 558, 237	4
120	Automated rf-PERTE System for Room Temperature Deposition of TCO Coatings. <i>Energy Procedia</i> , 2016 , 102, 96-101	2.3 4
119	A Simulation Study of Surface Plasmons in Metallic Nanoparticles: Dependence on the Properties of an Embedding a-Si:H Matrix. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700487	1.6 4
118	Analysis of metallic nanoparticles embedded in thin film semiconductors for optoelectronic applications. <i>Optical and Quantum Electronics</i> , 2018 , 50, 1	2.4 4
117	Semiconductor device as optical demultiplexer for short range optical communications. <i>Journal of Nanoscience and Nanotechnology</i> , 2011 , 11, 5318-22	1.3 3
116	Multilayer architectures based on a-SiC:H material: tunable wavelength filters in optical processing devices. <i>Journal of Nanoscience and Nanotechnology</i> , 2011 , 11, 5299-304	1.3 3
115	Double Pin Photodiodes with Two Optical Gate Connections for Light Triggering 2010 ,	3
114	Spectral response characterization of a-Si:H-based MIS-type photosensors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 3410-3413	3
113	a-SiC:H/a-Si:H tandem photodiodes: a numerical simulation. <i>Sensors and Actuators A: Physical</i> , 2004 , 113, 324-328	3.9 3
112	Sensor element for a metal-insulator-semiconductor camera system (MISCam). <i>Sensors and Actuators A: Physical</i> , 2004 , 115, 331-335	3.9 3
111	Bias-dependent photocurrent collection in p^+n a-Si:H/SiC:H heterojunction. <i>Sensors and Actuators A: Physical</i> , 2002 , 97-98, 221-226	3.9 3
110	A two terminal optical signal and image processing p^+n/p^+n image and colour sensor. <i>Sensors and Actuators A: Physical</i> , 2005 , 123-124, 331-336	3.9 3
109	p^+n flexible imaging devices with optical readout. <i>Optical Materials</i> , 2005 , 27, 1069-1073	3.3 3
108	Influence of the transducer configuration on the p-i-n image sensor resolution. <i>Thin Solid Films</i> , 2001 , 383, 65-68	2.2 3
107	VIS/NIR detector based on μ -Si:H p^+n structures. <i>Thin Solid Films</i> , 2000 , 364, 204-208	2.2 3

106	The contact geometry in a 2D β -Si:H p-i-n imager. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000 , 69-70, 494-499	3.1	3
105	Use of a-SiC:H Photodiodes in Optical Communications Applications 2011 ,		3
104	Plasmonic properties of gold nanospheres coupled to reduced graphene oxide for biosensing applications * 2019 ,		2
103	A Distributed SPICE Model for Amorphous Silicon Solar Cells. <i>Energy Procedia</i> , 2014 , 60, 96-101	2.3	2
102	Capacitive effects in pinpin photodiodes. <i>Microelectronic Engineering</i> , 2013 , 108, 195-199	2.5	2
101	Direct color sensor, optical amplifier and demux device integrated on a single monolithic SiC photodetector. <i>Procedia Engineering</i> , 2010 , 5, 232-235		2
100	Optical processing devices based on a-SiC:H multilayer architectures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, NA-NA		2
99	Multilayered a-SiC:H device for Wavelength-Division (de)Multiplexing applications in the visible spectrum. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1066, 1		2
98	Modeling and Characterization of the Hydrogenated Amorphous Silicon Metal Insulator Semiconductor Photosensors for Digital Radiography. <i>Materials Research Society Symposia Proceedings</i> , 2007 , 989, 6		2
97	Optical confinement and colour separation in a double colour laser scanned photodiode (D/CLSP). <i>Sensors and Actuators A: Physical</i> , 2004 , 114, 219-223	3.9	2
96	Memory effects in highly resistive p^+n heterojunctions for optical applications. <i>Thin Solid Films</i> , 2002 , 403-404, 363-367	2.2	2
95	Laser scanned photodiodes (LSPs) for image sensing. <i>Sensors and Actuators A: Physical</i> , 2002 , 97-98, 98-103		2
94	Electrical simulation of a p^+n image sensor. <i>Vacuum</i> , 2002 , 64, 307-313	3.7	2
93	Bias controlled spectral sensitivity in a-SiC:H p^+n devices. <i>Thin Solid Films</i> , 2003 , 427, 196-200	2.2	2
92	Non-pixeled amorphous silicon-based image sensors. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003 , 16, 563-567	3	2
91	Enhanced short wavelength response in laser-scanned-photodiode image sensor using an a-SiC:H/a-Si:H tandem structure. <i>Sensors and Actuators A: Physical</i> , 2005 , 123-124, 343-348	3.9	2
90	Flying Spot Technique in Microcrystalline Silicon Solar Cells. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 609, 3241		2
89	β -Si:H Thin-Film Devices for Optical Image Recognition. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 508, 145		2

88	Visible-infrared spectral response of microcrystalline hydrogenated silicon hetero-junctions. <i>Vacuum</i> , 1999 , 52, 121-124	3.7	2
87	Anisotropic Transport in Microcrystalline P-I-N Devices. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 557, 549		2
86	Long-Term Stability of Microcrystalline Silicon P-I-N Solar Cells Exposed to Sun Light. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 557, 597		2
85	Etchability Dependence of InOx and ITO Thin Films by Plasma Enhanced Reactive Thermal Evaporation on Structural Properties and Deposition Conditions. <i>MRS Advances</i> , 2018 , 3, 207-212	0.7	1
84	Preparation and Characterization of a-SiC:H Absorber Layer for Semi-transparent Solar Cells. <i>Energy Procedia</i> , 2015 , 84, 56-61	2.3	1
83	Driving Scheme Using MIS Photosensor for Luminance Control of AMOLED Pixel. <i>Journal of Display Technology</i> , 2013 , 9, 651-655		1
82	Photo-sensing devices using a-Si based materials. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 1079-1082		1
81	Electronic detection and quantification of ions in solution using an a-Si:H field-effect device. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1153, 1		1
80	Modeling a-SiC:H tandem pinpin and pinip photodiodes for color sensor application. <i>Journal of Nanoscience and Nanotechnology</i> , 2009 , 9, 4028-33	1.3	1
79	Photodiode with nanocrystalline Si/amorphous Si absorber bilayer. <i>Applied Physics Letters</i> , 2011 , 99, 1913-14	1.1	1
78	Self optical gain in multilayered silicon-carbon heterostructures: A capacitive active band-pass filter model. <i>Materials Research Society Symposia Proceedings</i> , 2011 , 1321, 441		1
77	Optical demultiplexer based on an a-SiC:H voltage controlled device. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, NA-NA		1
76	Transient current in a-Si:H-based MIS photosensors. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1066, 1		1
75	Analysis and simulation of a-Si:H/a-SiC:H PINIP structures for color image detection. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2069-2074	1.6	1
74	Preliminary Results on Large Area X-ray a-SiC:H Multilayer Detectors with Optically Addressed Readout. <i>Materials Research Society Symposia Proceedings</i> , 2007 , 989, 2		1
73	Light filtering in a-SiC:H multilayers stacked devices using the LSP technique. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 1809-1812	3.9	1
72	Spice model for a laser scanned photodiode tricolor image sensor. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 1813-1817	3.9	1
71	Colour filtering in a-SiC:H based p-i-n-p-i-n cells: A trade-off between bias polarity and absorption regions. <i>Sensors and Actuators A: Physical</i> , 2006 , 132, 218-223	3.9	1

70	Stacked a-SiC:H Optical Transducers: the Influence of the Sensing Material. <i>Materials Science Forum</i> , 2004 , 455-456, 81-85	0.4	1
69	Large area p-i-n flexible image sensors. <i>Materials Research Society Symposia Proceedings</i> , 2004 , 814, 260		1
68	Novel structure for large area image sensing. <i>Sensors and Actuators A: Physical</i> , 2004 , 115, 357-361	3.9	1
67	Tuning the spectral distribution of p-i-n a-SiC:H devices for colour detection. <i>Sensors and Actuators A: Physical</i> , 2005 , 120, 88-93	3.9	1
66	Spectral Sensitivity and Color Selectivity in Multilayer Stacked Devices. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 862, 921		1
65	Optimized Laser Scanned Photodiode (LSP) Imaging Transducer. <i>Physica Status Solidi A</i> , 2001 , 185, 129-135		1
64	From Intelligent Materials to Smart Sensors: a-Si:H Position Sensitive Detectors. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 420, 165		1
63	Simulation of localized surface plasmon in metallic nanoparticles embedded in amorphous silicon 2017 ,		1
62	A simulation analysis for dimensioning of an amorphous silicon planar waveguide structure suitable to be used as a surface plasmon resonance biosensor 2019 ,		1
61	Photoconductivity kinetics of indium sulfide thin films. <i>EPJ Applied Physics</i> , 2020 , 89, 10302	1.1	1
60	Bias dependent photocurrent collection in p-i-n a-Si:H/SiC:H heterojunction 2001 , 540-543		1
59	Characterization of Plasmonic Effects in AuNP+rGO Composite as a Sensing Layer for a Low-cost Lab-on-chip Biosensor 2019 ,		1
58	Conducting indium oxide films on plastic substrates by plasma enhanced reactive thermal evaporation. <i>Thin Solid Films</i> , 2019 , 691, 137604	2.2	0
57	Local Surface Plasmon Resonance of metallic nanoparticles embedded in amorphous silicon. <i>Ciência & Tecnologia Dos Materiais</i> , 2017 , 29, e146-e150		0
56	Electrical, optical and photoconductive properties of Sn-doped indium sulfide thin films. <i>Materials Science in Semiconductor Processing</i> , 2021 , 121, 105349	4.3	0
55	PINPIN a-Si:H based structures for X-ray image detection using the laser scanning technique. <i>Applied Surface Science</i> , 2015 , 336, 222-225	6.7	
54	MIS Sensor for Luminance Control of AMOLED Pixel. <i>Procedia Technology</i> , 2014 , 17, 574-579		
53	Characterization of a-Si:H Solar Cell Modules on Plastic Substrates by High Resolution LBIC Technique. <i>Energy Procedia</i> , 2015 , 84, 93-98	2.3	

- 52 Automated PECVD System for Fabrication of a-Si:H Devices. *Procedia Technology*, **2014**, 17, 580-586
- 51 Optimization of the protocrystalline p-layer in a-Si:H-based n-i-p photodiodes. *Materials Research Society Symposia Proceedings*, **2014**, 1666, 59
- 50 Thin-Film Phototransistor with nc-Si:H/a-Si:H Bilayer Channel. *Materials Research Society Symposia Proceedings*, **2012**, 1426, 205-210
- 49 Detection of change in fluorescence between reactive cyan and the yellow fluorophores using a-SiC:H multilayer transducers. *Journal of Nanoscience and Nanotechnology*, **2011**, 11, 8657-62 1.3
- 48 Membrane selectivity versus sensor response in hydrogenated amorphous silicon CHEMFETs using a semi-empirical model. *Journal of Nanoscience and Nanotechnology*, **2011**, 11, 8844-7 1.3
- 47 Light-triggered silicon-carbon pi-npin devices with self amplification. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1083-1086
- 46 Demultiplexer/Photodetector Integrated System Based on a-SiC:H Multilayered Structures. *Materials Research Society Symposia Proceedings*, **2010**, 1245, 1
- 45 Reviewing Photo-sensing Devices Using a-SiC Based Materials. *Materials Research Society Symposia Proceedings*, **2010**, 1245, 1
- 44 a-SiC:H Based Devices as Optical Demultiplexers. *Materials Research Society Symposia Proceedings*, **2010**, 1246, 1
- 43 Monolithic a-SiC:H stack architectures as tunable optical filters for spectral analysis. *Materials Research Society Symposia Proceedings*, **2010**, 1246, 1
- 42 Light-triggered Silicon-carbon Pi-npin Devices for Optical Communications: Theoretical and Electrical Approaches. *Materials Research Society Symposia Proceedings*, **2010**, 1245, 1
- 41 Fine Tuning of the Spectral Sensitivity in a-SiC:H Stacked p-i-n Graded Cells. *Materials Research Society Symposia Proceedings*, **2009**, 1153, 1
- 40 Optical Processing Devices for Optical Communications: Multilayered a-SiC:H Architectures. *Materials Research Society Symposia Proceedings*, **2009**, 1153, 1
- 39 a-Si:H pi-n structures with extreme i-layer thickness. *Thin Solid Films*, **2009**, 517, 6426-6429 2.2
- 38 Optical bias controlled amplification in tandem Si-C pinpin devices. *Materials Research Society Symposia Proceedings*, **2011**, 1321, 417
- 37 Use of a-SiC:H multilayer transducers for detection of fluorescence signals from reactive cyan and yellow fluorophores. *Materials Research Society Symposia Proceedings*, **2011**, 1321, 223
- 36 DEMUX SiC optical transducers for fluorescent proteins detection. *Materials Research Society Symposia Proceedings*, **2011**, 1324, 137
- 35 Three Transducers Embedded into a Single SiC Photodetector: LSP Direct Image Sensor, Optical Amplifier and Demux. *Journal of Nano Research*, **2012**, 18-19, 265-270 1

- 34 Photocurrent and spectral response analysis of a-SiC:H pinip and pinpin photodiodes. *Journal of Nanoscience and Nanotechnology*, **2009**, 9, 4254-8 1.3
- 33 Optical demultiplexer device operating in the visible spectrum. *Procedia Engineering*, **2010**, 5, 657-660
- 32 Non-selective optical wavelength-division multiplexing devices based on a-SiC:H multilayer heterostuctures. *Materials Research Society Symposia Proceedings*, **2008**, 1076, 1
- 31 Improvement in pinpin Device Architectures for Imaging Applications. *Materials Research Society Symposia Proceedings*, **2008**, 1066, 1
- 30 Light Filtering Properties in a-SiC:H Multilayer Structures: A SPICE model. *Materials Research Society Symposia Proceedings*, **2006**, 910, 1
- 29 Band Gap Engineering and Electrical Field Tailoring for Voltage Controlled Spectral Sensitivity. *Materials Research Society Symposia Proceedings*, **2006**, 910, 2
- 28 Modeling the Laser Scanned Photodiode S-shaped J-V Characteristic. *Materials Research Society Symposia Proceedings*, **2007**, 989, 3
- 27 a-SiC:H/a-Si:H tandem structure analysis for RGB color recognition in LSP devices. *Journal of Non-Crystalline Solids*, **2006**, 352, 1805-1808 3.9
- 26 Bias sensitive spectral sensitivity in double a-SiC:H pin structures. *Superlattices and Microstructures*, **2006**, 40, 619-625 2.8
- 25 Fine-tuning of the spectral collection efficiency in multilayer junctions. *Thin Solid Films*, **2006**, 511-512, 84-88 2.2
- 24 A real-time optical signal and image processing p-i-n/p-i-n device. *Materials Research Society Symposia Proceedings*, **2004**, 808, 257
- 23 High Sensitive Image Sensors Based on a Tandem Laser Scanned Photodiode. *Materials Science Forum*, **2004**, 455-456, 91-95 0.4
- 22 Large area single and stacked p-i-n photodiodes as a color image sensors. *Materials Research Society Symposia Proceedings*, **2004**, 815, 100
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- 20 Dynamic Characterization of Large Area Image Sensing Structures Based on a-SiC:H. *Materials Science Forum*, **2004**, 455-456, 86-90 0.4
- 19 A non-pixel image reader for continuous image detection based on tandem heterostructures. *Sensors and Actuators A: Physical*, **2004**, 115, 191-195 3.9
- 18 Biometric system based on one single large area a-SiC:H p-i-n photodiode. *Materials Research Society Symposia Proceedings*, **2002**, 722, 1061
- 17 Modelling a-Si:H based p-i-n structures for optical sensor applications. *Thin Solid Films*, **2002**, 403-404, 354-358 2.2

- 16 Analog readout image sensor based on p⁺i hydrogenated amorphous silicon. *Vacuum*, **2002**, 64, 249-254, 3.7
- 15 Optical signal and image processing device optimized for optical readout. *Optical Materials*, **2005**, 27, 1064-1068 3.3
- 14 Fine-Tuning of the Spectral Collection Efficiency in a Multilayer Junction Through the LSP Technique. *Materials Research Society Symposia Proceedings*, **2005**, 872, 1
- 13 Photocurrent response time scanner. *Journal of Non-Crystalline Solids*, **2002**, 299-302, 1261-1266 3.9
- 12 A 3-phase model for VIS/NIR α -Si:H p⁺i detectors. *Sensors and Actuators A: Physical*, **2000**, 85, 175-180 3.9
- 11 A three-path model for visible/near infrared β -Si:H p⁺i detectors. *Journal of Non-Crystalline Solids*, **2000**, 266-269, 1223-1227 3.9
- 10 Charge Carrier Transport in a-Si:H/a-SiC:H Heterojunction with Blocking Layer. *Materials Research Society Symposia Proceedings*, **2001**, 685, 1
- 9 Image Acquisition Using Non-Pixelated Amorphous Silicon Based Sensors. *Materials Research Society Symposia Proceedings*, **2001**, 685, 1
- 8 Effect of a-SiC:H Film Composition on the Performance of Large Area Optical Sensors. *Materials Research Society Symposia Proceedings*, **2001**, 685, 1
- 7 Laser scanned photodiodes (LSP) for Image sensing **2001**, 578-581
- 6 Analysis of the Bias Dependent Spectral Response of a-SiC:H p-i-n Photodiode. *Materials Research Society Symposia Proceedings*, **2002**, 715, 731
- 5 Dynamic Response of Non-Pixelated Amorphous Silicon Based Image Sensors. *Materials Research Society Symposia Proceedings*, **2002**, 722, 911
- 4 Finite-difference time-domain analysis of hydrogenated amorphous silicon and aluminum surface plasmon waveguides. *Optical Engineering*, **2018**, 57, 1 1.1
- 3 Optical Transducers Based on Amorphous Si/SiC Photodiodes. *International Federation for Information Processing*, **2011**, 604-611
- 2 Simulation in Amorphous Silicon and Amorphous Silicon Carbide Pin Diodes. *IFIP Advances in Information and Communication Technology*, **2014**, 602-609 0.5
- 1 Amorphous Silicon Photovoltaic Modules on Flexible Plastic Substrates. *MRS Advances*, **2016**, 1, 2923-2928